

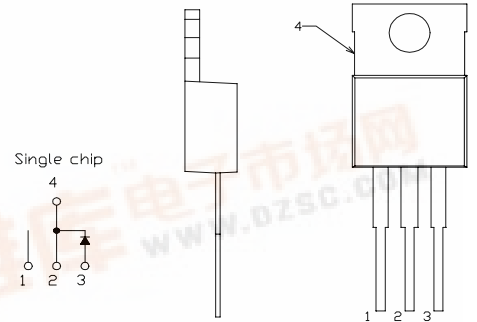


# FRD Type : GSF10A20B

## OUTLINE DRAWING

### FEATURES

- \* Similar to TO-220AB Case
- \* Ultra – Fast Recovery
- \* Low Forward Voltage Drop
- \* Low Power Loss, High Efficiency
- \* High Surge Capability
- \* 200 Volts thru 600 Volts Types Available



### Maximum Ratings

Approx Net Weight:1.9g

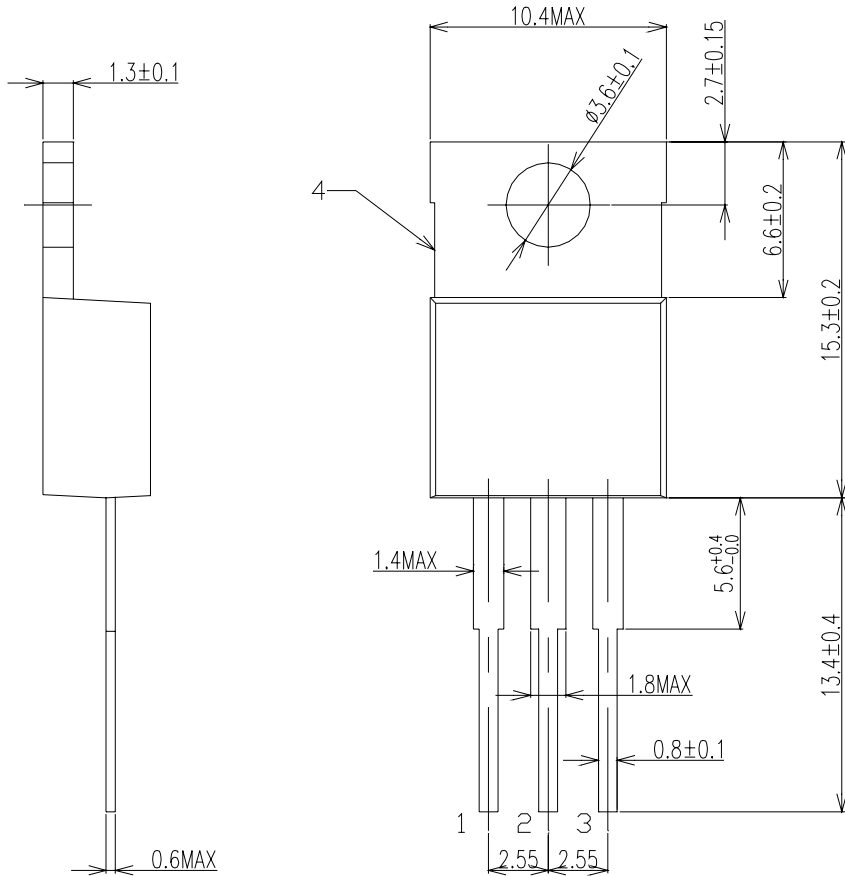
Rating	Symbol	GSF10A20B		Unit
Repetitive Peak Reverse Voltage	$V_{RRM}$	200		V
Non-repetitive Peak Reverse Voltage	$V_{RSM}$	220		
Average Rectified Output Current	$I_O$	10	$T_c=100^\circ\text{C}$ 50 Hz Half Sine Wave Resistive Load	A
RMS Forward Current	$I_{F(RMS)}$	15.7		A
Surge Forward Current	$I_{FSM}$	120	50 Hz Half Sine Wave, 1cycle Non-repetitive	A
Operating Junction Temperature Range	$T_{jw}$	- 40 to + 150		$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	- 40 to + 150		$^\circ\text{C}$
Mounting torque		0.5	Recommended value	N·m

### Electrical • Thermal Characteristics

Characteristics	Symbol	Conditions	Min.	Typ.	Max.	Unit
Peak Reverse Current	$I_{RM}$	$T_j= 25^\circ\text{C}, V_{RM}= V_{RRM}$	-	-	25	$\mu\text{A}$
Peak Forward Voltage	$V_{FM}$	$T_j= 25^\circ\text{C}, I_{FM}= 10\text{A}$	-	-	1.03	V
Reverse Recovery Time	$t_{rr}$	$I_{FM}= 10\text{A},$ $-di/dt= 50 \text{ A}/\mu\text{s}, T_a= 25^\circ\text{C}$	-	-	35	ns
Thermal Resistance	$R_{th(j-c)}$	Junction to Case	-	-	4	$^\circ\text{C}/\text{W}$



GSF10A20B OUTLINE DRAWING (Dimensions in mm)



Single chip

